

Hiroki Hibino

List of Publications by Year in Descending Order

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The third column is the impact factor (IF) of the journal, and the fourth column is the number of citations of the article.

223
papers

5,926
citations

37
h-index

67
g-index

246
ext. papers

6,389
ext. citations

4.5
avg, IF

5.73
L-index

#	Paper	IF	Citations
223	Theoretical study on role of edge termination for growth direction selectivity in chemical vapor deposition of hBN/graphene heterostructure on Cu surface. <i>Applied Physics Express</i> , 2021 , 14, 085502	2.4	2
222	Epitaxial Intercalation Growth of Scalable Hexagonal Boron Nitride/Graphene Bilayer Moiré Materials with Highly Convergent Interlayer Angles. <i>ACS Nano</i> , 2021 , 15, 14384-14393	16.7	5
221	Controlled CVD growth of lateral and vertical graphene/h-BN heterostructures. <i>Applied Physics Express</i> , 2020 , 13, 065007	2.4	7
220	In-situ X-ray diffraction analysis of GaN growth on graphene-covered amorphous substrates. <i>Japanese Journal of Applied Physics</i> , 2020 , 59, 070902	1.4	3
219	Isothermal Growth and Stacking Evolution in Highly Uniform Bernal-Stacked Bilayer Graphene. <i>ACS Nano</i> , 2020 , 14, 6834-6844	16.7	17
218	Surface-enhanced Raman scattering from buffer layer under graphene on SiC in a wide energy range from visible to near-infrared. <i>Japanese Journal of Applied Physics</i> , 2020 , 59, 040902	1.4	2
217	Quantum limit cyclotron resonance in monolayer epitaxial graphene in magnetic fields up to 560 T: The relativistic electron and hole asymmetry. <i>Physical Review B</i> , 2020 , 101,	3.3	3
216	Theoretical Study on C Adsorbate at Graphene/Cu(111) or h-BN/Cu(111) Interfaces. <i>E-Journal of Surface Science and Nanotechnology</i> , 2020 , 18, 70-75	0.7	3
215	Visualization of three different phases in a multiphase steel by scanning electron microscopy at 1 eV landing energy. <i>Ultramicroscopy</i> , 2019 , 204, 1-5	3.1	2
214	Catalyst-Selective Growth of Single-Orientation Hexagonal Boron Nitride toward High-Performance Atomically Thin Electric Barriers. <i>Advanced Materials</i> , 2019 , 31, e1900880	24	13
213	Synthesis of sub-millimeter single-crystal grains of aligned hexagonal boron nitride on an epitaxial Ni film. <i>Nanoscale</i> , 2019 , 11, 14668-14675	7.7	7
212	STM/S observations of graphene on SiC(0001) etched by H-plasma. <i>Japanese Journal of Applied Physics</i> , 2019 , 58, S11A13	1.4	0
211	Dopamine detection on activated reaction field consisting of graphene-integrated silicon photonic cavity. <i>Optics Express</i> , 2019 , 27, 32058-32068	3.3	5
210	In-situ Observations of Growth of 2D Layered Materials using Low-Energy Electron Microscopy. <i>Vacuum and Surface Science</i> , 2019 , 62, 623-628	0	
209	Ultrafast Terahertz Nonlinear Optics of Landau Level Transitions in a Monolayer Graphene. <i>Physical Review Letters</i> , 2018 , 120, 107401	7.4	4
208	Graphene nanoribbon field-effect transistors fabricated by etchant-free transfer from Au(788). <i>Applied Physics Letters</i> , 2018 , 112, 021602	3.4	22
207	Unraveling localized states in quasi free standing monolayer graphene by means of Density Functional Theory. <i>Carbon</i> , 2018 , 130, 466-474	10.4	6

206	Grain Boundaries and Gas Barrier Property of Graphene Revealed by Dark-Field Optical Microscopy. <i>Journal of Physical Chemistry C</i> , 2018 , 122, 902-910	3.8	8
205	Atomic and electronic structure of Si dangling bonds in quasi-free-standing monolayer graphene. <i>Nano Research</i> , 2018 , 11, 864-873	10	12
204	Surface-Mediated Aligned Growth of Monolayer MoS and In-Plane Heterostructures with Graphene on Sapphire. <i>ACS Nano</i> , 2018 , 12, 10032-10044	16.7	42
203	Surface structures of graphene covered Cu(103). <i>Japanese Journal of Applied Physics</i> , 2018 , 57, 100301	1.4	
202	Orientation-controlled growth of hexagonal boron nitride monolayers templated from graphene edges. <i>Applied Physics Express</i> , 2017 , 10, 055102	2.4	15
201	Behavior and role of superficial oxygen in Cu for the growth of large single-crystalline graphene. <i>Applied Surface Science</i> , 2017 , 408, 142-149	6.7	25
200	Very Gradual and Anomalous Oxidation at the Interface of Hydrogen-Intercalated Graphene/4H-SiC(0001). <i>Journal of Physical Chemistry C</i> , 2017 , 121, 26389-26396	3.8	0
199	Effects of environmental conditions on the ultrafast carrier dynamics in graphene revealed by terahertz spectroscopy. <i>Physical Review B</i> , 2017 , 95,	3.3	11
198	Spatially Controlled Nucleation of Single-Crystal Graphene on Cu Assisted by Stacked Ni. <i>ACS Nano</i> , 2016 , 10, 11196-11204	16.7	35
197	Atmospheric Pressure Chemical Vapor Deposition Growth of Millimeter-Scale Single-Crystalline Graphene on the Copper Surface with a Native Oxide Layer. <i>Chemistry of Materials</i> , 2016 , 28, 4893-4900	9.6	41
196	Growth and low-energy electron microscopy characterizations of graphene and hexagonal boron nitride. <i>Progress in Crystal Growth and Characterization of Materials</i> , 2016 , 62, 155-176	3.5	17
195	Highly Uniform Bilayer Graphene on Epitaxial CuNi(111) Alloy. <i>Chemistry of Materials</i> , 2016 , 28, 4583-4592	26	75
194	Energy Dissipation in Graphene Mechanical Resonators with and without Free Edges. <i>Micromachines</i> , 2016 , 7,	3.3	8
193	Theoretical Study of Graphene on SiC(11-20) a-Face. <i>E-Journal of Surface Science and Nanotechnology</i> , 2016 , 14, 113-120	0.7	1
192	Direct growth of graphene on SiC(0001) by KrF-excimer-laser irradiation. <i>Applied Physics Letters</i> , 2016 , 108, 093107	3.4	6
191	Quantum Hall effect in epitaxial graphene with permanent magnets. <i>Scientific Reports</i> , 2016 , 6, 38393	4.9	9
190	Ultra-fine metal gate operated graphene optical intensity modulator. <i>Applied Physics Letters</i> , 2016 , 109, 251101	3.4	9
189	Applying strain into graphene by SU-8 resist shrinkage. <i>Journal Physics D: Applied Physics</i> , 2016 , 49, 285303	3	2

188	Etchant-free graphene transfer using facile intercalation of alkanethiol self-assembled molecules at graphene/metal interfaces. <i>Nanoscale</i> , 2016 , 8, 11503-10	7.7	9
187	Graphene FRET Aptasensor. <i>ACS Sensors</i> , 2016 , 1, 710-716	9.2	23
186	Large optical anisotropy for terahertz light of stacked graphene ribbons with slight asymmetry. <i>Journal of Applied Physics</i> , 2015 , 117, 174302	2.5	2
185	Growth Dynamics of Single-Layer Graphene on Epitaxial Cu Surfaces. <i>Chemistry of Materials</i> , 2015 , 27, 5377-5385	9.6	50
184	Bilayer-induced asymmetric quantum Hall effect in epitaxial graphene. <i>Semiconductor Science and Technology</i> , 2015 , 30, 055007	1.8	5
183	Growth and Optical Properties of High-Quality Monolayer WS ₂ on Graphite. <i>ACS Nano</i> , 2015 , 9, 4056-63	16.7	129
182	Shot noise generated by graphene p-n junctions in the quantum Hall effect regime. <i>Nature Communications</i> , 2015 , 6, 8068	17.4	32
181	On-chip graphene oxide aptasensor for multiple protein detection. <i>Analytica Chimica Acta</i> , 2015 , 866, 1-9	6.6	36
180	Probing the extended-state width of disorder-broadened Landau levels in epitaxial graphene. <i>Physical Review B</i> , 2015 , 92,	3.3	12
179	On-chip FRET Graphene Oxide Aptasensor: Quantitative Evaluation of Enhanced Sensitivity by Aptamer with a Double-stranded DNA Spacer. <i>Analytical Sciences</i> , 2015 , 31, 875-9	1.7	14
178	Photocurrent generation of a single-gate graphene p-n junction fabricated by interfacial modification. <i>Nanotechnology</i> , 2015 , 26, 385203	3.4	13
177	2015 ,		1
176	Effects of UV light intensity on electrochemical wet etching of SiC for the fabrication of suspended graphene. <i>Japanese Journal of Applied Physics</i> , 2015 , 54, 036502	1.4	3
175	Nonlinear terahertz field-induced carrier dynamics in photoexcited epitaxial monolayer graphene. <i>Physical Review B</i> , 2015 , 91,	3.3	53
174	Direct chemical vapor deposition growth of WS ₂ atomic layers on hexagonal boron nitride. <i>ACS Nano</i> , 2014 , 8, 8273-7	16.7	234
173	Ultrathin Chemical Vapor Deposition (CVD)-Grown Hexagonal Boron Nitride as a High-Quality Dielectric for Tunneling Devices on Rigid and Flexible Substrates. <i>Journal of Physical Chemistry C</i> , 2014 , 118, 3340-3346	3.8	23
172	Raman spectroscopic investigation of polycrystalline structures of CVD-grown graphene by isotope labeling. <i>Nanoscale</i> , 2014 , 6, 13838-44	7.7	18
171	Formation of Oriented Graphene Nanoribbons over Heteroepitaxial Cu Surfaces by Chemical Vapor Deposition. <i>Chemistry of Materials</i> , 2014 , 26, 5215-5222	9.6	7

170	Optical absorption characteristics and polarization dependence of single-layer graphene on silicon waveguide. <i>IEICE Transactions on Electronics</i> , 2014 , E97.C, 736-743	0.4	
169	In situscanning electron microscopy of graphene nucleation during segregation of carbon on polycrystalline Ni substrate. <i>Journal Physics D: Applied Physics</i> , 2014 , 47, 455301	3	10
168	Plasmon transport and its guiding in graphene. <i>New Journal of Physics</i> , 2014 , 16, 063055	2.9	8
167	Nonlinear transmission of an intense terahertz field through monolayer graphene. <i>AIP Advances</i> , 2014 , 4, 117118	1.5	20
166	Correlation between morphology and transport properties of quasi-free-standing monolayer graphene. <i>Applied Physics Letters</i> , 2014 , 105, 221604	3.4	18
165	Etchant-free and damageless transfer of monolayer and bilayer graphene grown on SiC. <i>Japanese Journal of Applied Physics</i> , 2014 , 53, 115101	1.4	10
164	Scalable synthesis of layer-controlled WS ₂ and MoS ₂ sheets by sulfurization of thin metal films. <i>Applied Physics Letters</i> , 2014 , 105, 083112	3.4	94
163	Energy dissipation in edged and edgeless graphene mechanical resonators. <i>Journal of Applied Physics</i> , 2014 , 116, 064304	2.5	8
162	Influence of graphene on quality factor variation in a silicon ring resonator. <i>Applied Physics Letters</i> , 2014 , 104, 091122	3.4	14
161	Effects of hydrogen intercalation on transport properties of quasi-free-standing monolayer graphene. <i>Japanese Journal of Applied Physics</i> , 2014 , 53, 04EN01	1.4	16
160	Stability and Reactivity of [11-20] Step in Initial Stage of Epitaxial Graphene Growth on SiC(0001). <i>Materials Science Forum</i> , 2014 , 778-780, 1150-1153	0.4	
159	Resonant edge magnetoplasmons and their decay in graphene. <i>Physical Review Letters</i> , 2014 , 113, 266601	14	36
158	Surface-Enhanced Raman Scattering of Graphene on SiC by Gold Nanoparticles. <i>The Review of Laser Engineering</i> , 2014 , 42, 652	0	1
157	Boron nitride growth on metal foil using solid sources. <i>Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics</i> , 2013 , 31, 041804	1.3	15
156	Hydrogen storage with titanium-functionalized graphene. <i>Applied Physics Letters</i> , 2013 , 103, 013903	3.4	47
155	Site-Selective Epitaxy of Graphene on Si Wafers. <i>Proceedings of the IEEE</i> , 2013 , 101, 1557-1566	14.3	13
154	Molecular design for enhanced sensitivity of a FRET aptasensor built on the graphene oxide surface. <i>Chemical Communications</i> , 2013 , 49, 10346-8	5.8	27
153	Core-level photoelectron spectroscopy study of interface structure of hydrogen-intercalated graphene on n-type 4H-SiC(0001). <i>Physical Review B</i> , 2013 , 88,	3.3	11

152	Structural Instability of Transferred Graphene Grown by Chemical Vapor Deposition against Heating. <i>Journal of Physical Chemistry C</i> , 2013 , 117, 22123-22130	3.8	21
151	Lattice-oriented catalytic growth of graphene nanoribbons on heteroepitaxial nickel films. <i>ACS Nano</i> , 2013 , 7, 10825-33	16.7	27
150	Graphene-Based Nano-Electro-Mechanical Switch with High On/Off Ratio. <i>Applied Physics Express</i> , 2013 , 6, 055101	2.4	21
149	Plasmon transport in graphene investigated by time-resolved electrical measurements. <i>Nature Communications</i> , 2013 , 4, 1363	17.4	39
148	Molecular beam epitaxial growth of graphene using cracked ethylene. <i>Journal of Crystal Growth</i> , 2013 , 378, 404-409	1.6	2
147	Molecular beam epitaxial growth of graphene using cracked ethylene [Advantage over ethanol in growth. <i>Diamond and Related Materials</i> , 2013 , 34, 84-88	3.5	10
146	Protein recognition on a single graphene oxide surface fixed on a solid support. <i>Journal of Materials Chemistry B</i> , 2013 , 1, 1119-1124	7.3	26
145	Growth and low-energy electron microscopy characterization of monolayer hexagonal boron nitride on epitaxial cobalt. <i>Nano Research</i> , 2013 , 6, 335-347	10	93
144	Quantum Faraday and Kerr rotations in graphene. <i>Nature Communications</i> , 2013 , 4, 1841	17.4	126
143	Graphene Layer Formation on Polycrystalline Nickel Grown by Chemical Vapor Deposition. <i>Japanese Journal of Applied Physics</i> , 2013 , 52, 035103	1.4	12
142	Epitaxial Trilayer Graphene Mechanical Resonators Obtained by Electrochemical Etching Combined with Hydrogen Intercalation. <i>Japanese Journal of Applied Physics</i> , 2013 , 52, 04CH01	1.4	11
141	Characterization of Optical Absorption and Polarization Dependence of Single-Layer Graphene Integrated on a Silicon Wire Waveguide. <i>Japanese Journal of Applied Physics</i> , 2013 , 52, 060203	1.4	18
140	Self organization of a hexagonal network of quasi-free-standing monolayer graphene nanoribbons. <i>Physical Review B</i> , 2013 , 87,	3.3	3
139	Stability and reactivity of steps in the initial stage of graphene growth on the SiC(0001) surface. <i>Physical Review B</i> , 2013 , 88,	3.3	15
138	Selective charge doping of chemical vapor deposition-grown graphene by interface modification. <i>Applied Physics Letters</i> , 2013 , 103, 253116	3.4	14
137	Tuning of quantum interference in top-gated graphene on SiC. <i>Physical Review B</i> , 2013 , 88,	3.3	14
136	Graphene-modified interdigitated array electrode: fabrication, characterization, and electrochemical immunoassay application. <i>Analytical Sciences</i> , 2013 , 29, 55-60	1.7	22
135	Chemical vapor deposition of boron- and nitrogen-containing graphene thin films. <i>Materials Science and Engineering B: Solid-State Materials for Advanced Technology</i> , 2012 , 177, 233-238	3.1	23

134	Self-spreading of Supported Lipid Bilayer on SiO ₂ Surface Bearing Graphene Oxide. <i>Chemistry Letters</i> , 2012 , 41, 1259-1261	1.7	17
133	Catalytic Growth of Graphene: Toward Large-Area Single-Crystalline Graphene. <i>Journal of Physical Chemistry Letters</i> , 2012 , 3, 2228-36	6.4	120
132	Growth and electronic transport properties of epitaxial graphene on SiC. <i>Journal Physics D: Applied Physics</i> , 2012 , 45, 154008	3	36
131	In situ scanning electron microscopy of graphene growth on polycrystalline Ni substrate. <i>Surface Science</i> , 2012 , 606, 728-732	1.8	49
130	A Raman imaging study of growth process of few-layer epitaxial graphene on vicinal 6H-SiC. <i>Diamond and Related Materials</i> , 2012 , 25, 80-83	3.5	2
129	Domain Structure and Boundary in Single-Layer Graphene Grown on Cu(111) and Cu(100) Films. <i>Journal of Physical Chemistry Letters</i> , 2012 , 3, 219-226	6.4	186
128	Macroscopic Single-Domain Graphene Growth on Polycrystalline Nickel Surface. <i>Applied Physics Express</i> , 2012 , 5, 035501	2.4	18
127	Spatially Resolved Compositional Analysis of a BCN Thin Film Grown on a Ni Substrate by Chemical Vapor Deposition. <i>Materials Research Society Symposia Proceedings</i> , 2012 , 1451, 151-156		
126	Growth of atomically thin hexagonal boron nitride films by diffusion through a metal film and precipitation. <i>Journal Physics D: Applied Physics</i> , 2012 , 45, 385304	3	37
125	Chemical Vapor Deposition of Hexagonal Boron Nitride. <i>E-Journal of Surface Science and Nanotechnology</i> , 2012 , 10, 133-138	0.7	13
124	Influence of Cu metal on the domain structure and carrier mobility in single-layer graphene. <i>Carbon</i> , 2012 , 50, 2189-2196	10.4	78
123	Electrical Characterization of Bilayer Graphene Formed by Hydrogen Intercalation of Monolayer Graphene on SiC(0001). <i>Japanese Journal of Applied Physics</i> , 2012 , 51, 02BN02	1.4	15
122	Impact of graphene quantum capacitance on transport spectroscopy. <i>Physical Review B</i> , 2012 , 86,	3.3	23
121	Quantum Hall Effect and Carrier Scattering in Quasi-Free-Standing Monolayer Graphene. <i>Applied Physics Express</i> , 2012 , 5, 125101	2.4	23
120	The physics of epitaxial graphene on SiC(0001). <i>Journal of Physics Condensed Matter</i> , 2012 , 24, 314215	1.8	21
119	In-situ Observation of Graphene Growth on Ultra Flat Metal Substrates. <i>Hyomen Kagaku</i> , 2012 , 33, 557-562		
118	Electrical Characterization of Bilayer Graphene Formed by Hydrogen Intercalation of Monolayer Graphene on SiC(0001). <i>Japanese Journal of Applied Physics</i> , 2012 , 51, 02BN02	1.4	29
117	Microscopic Raman Mapping of Epitaxial Graphene on 4H-SiC(0001). <i>Japanese Journal of Applied Physics</i> , 2012 , 51, 06FD06	1.4	5

116	Formation of Graphene Nanofin Networks on Graphene/SiC(0001) by Molecular Beam Epitaxy. <i>Japanese Journal of Applied Physics</i> , 2012 , 51, 06FD16	1.4	1
115	Near-Infrared Photoluminescence Spectral Imaging of Chemically Oxidized Graphene Flakes. <i>E-Journal of Surface Science and Nanotechnology</i> , 2012 , 10, 513-517	0.7	1
114	Nanocarbon Materials Growth Dependent on Au Nanoparticle Catalyst Size. <i>Hyomen Kagaku</i> , 2012 , 33, 141-146		
113	Graphene Growth from Spin-Coated Polymers without a Gas. <i>Japanese Journal of Applied Physics</i> , 2012 , 51, 06FD01	1.4	1
112	Theoretical Study on Magnetoelectric and Thermoelectric Properties for Graphene Devices. <i>Japanese Journal of Applied Physics</i> , 2011 , 50, 070115	1.4	8
111	Characterization of doped single-wall carbon nanotubes by Raman spectroscopy. <i>Carbon</i> , 2011 , 49, 2264-2272	1.4	47
110	Study of Graphene Growth by Gas-Source Molecular Beam Epitaxy Using Cracked Ethanol: Influence of Gas Flow Rate on Graphitic Material Deposition. <i>Japanese Journal of Applied Physics</i> , 2011 , 50, 06GE12	1.4	7
109	Theoretical Study on Epitaxial Graphene Growth by Si Sublimation from SiC(0001) Surface. <i>Japanese Journal of Applied Physics</i> , 2011 , 50, 095601	1.4	7
108	Observation of Band Gap in Epitaxial Bilayer Graphene Field Effect Transistors. <i>Japanese Journal of Applied Physics</i> , 2011 , 50, 04DN04	1.4	13
107	Pattern formation of a step induced by a moving linear source. <i>Physical Review B</i> , 2011 , 84,	3.3	6
106	Carrier transport mechanism in graphene on SiC(0001). <i>Physical Review B</i> , 2011 , 84,	3.3	77
105	Graphene Growth from a Spin-Coated Polymer without a Reactive Gas. <i>Applied Physics Express</i> , 2011 , 4, 065102	2.4	16
104	Electronic transport properties of top-gated monolayer and bilayer graphene devices on SiC. <i>Materials Research Society Symposia Proceedings</i> , 2011 , 1283, 1		2
103	Molecular beam epitaxial growth of graphene and ridge-structure networks of graphene. <i>Journal Physics D: Applied Physics</i> , 2011 , 44, 435305	3	12
102	Evaluation of Few-Layer Graphene Grown by Gas-Source Molecular Beam Epitaxy Using Cracked Ethanol. <i>E-Journal of Surface Science and Nanotechnology</i> , 2011 , 9, 58-62	0.7	7
101	Observation of Band Gap in Epitaxial Bilayer Graphene Field Effect Transistors. <i>Japanese Journal of Applied Physics</i> , 2011 , 50, 04DN04	1.4	3
100	Study of Graphene Growth by Gas-Source Molecular Beam Epitaxy Using Cracked Ethanol: Influence of Gas Flow Rate on Graphitic Material Deposition. <i>Japanese Journal of Applied Physics</i> , 2011 , 50, 06GE12	1.4	22
99	Theoretical Study on Magnetoelectric and Thermoelectric Properties for Graphene Devices. <i>Japanese Journal of Applied Physics</i> , 2011 , 50, 070115	1.4	8

98	Theoretical Study on Epitaxial Graphene Growth by Si Sublimation from SiC(0001) Surface. <i>Japanese Journal of Applied Physics</i> , 2011 , 50, 095601	1.4	8
97	Atomic Structure and Physical Properties of Epitaxial Graphene Islands Embedded in SiC(0001) Surfaces. <i>Applied Physics Express</i> , 2010 , 3, 115103	2.4	9
96	Epitaxial Graphene Growth Studied by Low-Energy Electron Microscopy and First-Principles. <i>Materials Science Forum</i> , 2010 , 645-648, 597-602	0.4	11
95	Thin Graphitic Structure Formation on Various Substrates by Gas-Source Molecular Beam Epitaxy Using Cracked Ethanol. <i>Japanese Journal of Applied Physics</i> , 2010 , 49, 04DH13	1.4	22
94	Epitaxial few-layer graphene: towards single crystal growth. <i>Journal Physics D: Applied Physics</i> , 2010 , 43, 374005	3	96
93	Anisotropic layer-by-layer growth of graphene on vicinal SiC(0001) surfaces. <i>Physical Review B</i> , 2010 , 81,	3.3	93
92	Half-Integer Quantum Hall Effect in Gate-Controlled Epitaxial Graphene Devices. <i>Applied Physics Express</i> , 2010 , 3, 075102	2.4	58
91	Contact Conductance Measurement of Locally Suspended Graphene on SiC. <i>Applied Physics Express</i> , 2010 , 3, 045101	2.4	17
90	Growth of few-layer graphene by gas-source molecular beam epitaxy using cracked ethanol. <i>Physica Status Solidi (B): Basic Research</i> , 2010 , 247, NA-NA	1.3	3
89	Analysis of Number of Layers in Epitaxial Few-Layer Graphene Grown on SiC towards Single-Crystal Graphene Substrate. <i>Journal of the Vacuum Society of Japan</i> , 2010 , 53, 101-108		
88	Local conductance measurements of double-layer graphene on SiC substrate. <i>Nanotechnology</i> , 2009 , 20, 445704	3.4	36
87	Theoretical Study of Epitaxial Graphene Growth on SiC(0001) Surfaces. <i>Applied Physics Express</i> , 2009 , 2, 065502	2.4	59
86	Dependence of electronic properties of epitaxial few-layer graphene on the number of layers investigated by photoelectron emission microscopy. <i>Physical Review B</i> , 2009 , 79,	3.3	218
85	Stacking domains of epitaxial few-layer graphene on SiC(0001). <i>Physical Review B</i> , 2009 , 80,	3.3	74
84	A Lattice Model for Thermal Decoration and Step Bunching in Vicinal Surface with Sub-Monolayer Adsorbates. <i>E-Journal of Surface Science and Nanotechnology</i> , 2009 , 7, 39-44	0.7	9
83	Mechanism of gold-catalyzed carbon material growth. <i>Nano Letters</i> , 2008 , 8, 832-5	11.5	102
82	In-plane conductance measurement of graphene nanoislands using an integrated nanogap probe. <i>Nanotechnology</i> , 2008 , 19, 495701	3.4	20
81	Microscopic thickness determination of thin graphite films formed on SiC from quantized oscillation in reflectivity of low-energy electrons. <i>Physical Review B</i> , 2008 , 77,	3.3	301

80	Local conductance measurement of few-layer graphene on SiC substrate using an integrated nanogap probe. <i>Journal of Physics: Conference Series</i> , 2008 , 100, 052006	0.3	7
79	Thickness Determination of Graphene Layers Formed on SiC Using Low-Energy Electron Microscopy. <i>E-Journal of Surface Science and Nanotechnology</i> , 2008 , 6, 107-110	0.7	41
78	Two-dimensional emission patterns of secondary electrons from graphene layers formed on SiC(0001). <i>Applied Surface Science</i> , 2008 , 254, 7596-7599	6.7	18
77	Instability of steps during Ga deposition on Si(1 1 1). <i>Surface Science</i> , 2008 , 602, 2421-2426	1.8	12
76	Oxide-mediated formation of β -FeSi ₂ on Si(001) studied by X-ray adsorption near edge structure analysis using SPELEEM. <i>Surface and Interface Analysis</i> , 2008 , 40, 1747-1750	1.5	3
75	Carbon nanotube growth from semiconductor nanoparticles. <i>Nano Letters</i> , 2007 , 7, 2272-5	11.5	203
74	Self-assembly of vesicle nanoarrays on Si: A potential route to high-density functional protein arrays. <i>Applied Physics Letters</i> , 2007 , 90, 033901	3.4	4
73	Boron Nitride Thin Films Grown on Graphitized 6H-SiC Substrates by Metalorganic Vapor Phase Epitaxy. <i>Japanese Journal of Applied Physics</i> , 2007 , 46, 2554-2557	1.4	12
72	Surface Reactions of Metal Catalysts for Carbon Nanotubes on an Oxide Thin Layer/Si Substrates Studied by in-situ Micro X-ray Adsorption Spectroscopy using SPELEEM. <i>Materials Research Society Symposia Proceedings</i> , 2006 , 967, 1		
71	Void growth during thermal decomposition of silicon oxide layers studied by low-energy electron microscopy. <i>Journal of Applied Physics</i> , 2006 , 100, 113519	2.5	37
70	Vertical GaP nanowires arranged at atomic steps on Si(111) substrates. <i>Applied Physics Letters</i> , 2006 , 89, 033114	3.4	31
69	Single-walled carbon nanotube growth from highly activated metal nanoparticles. <i>Nano Letters</i> , 2006 , 6, 2642-5	11.5	389
68	Surface Reactions of Co on SiO ₂ thin layer/Si substrate Studied by LEEM and PEEM. <i>E-Journal of Surface Science and Nanotechnology</i> , 2006 , 4, 155-160	0.7	6
67	Arrangement of Au ₃ Bi alloy islands at atomic steps. <i>Surface Science</i> , 2005 , 588, L233-L238	1.8	22
66	Ultrahigh vacuum scanning electron microscope system combined with wide-movable scanning tunneling microscope. <i>Review of Scientific Instruments</i> , 2005 , 76, 083709	1.7	6
65	Growth of Twinned Epitaxial Layers on Si(111) $\sqrt{3}\times\sqrt{3}$ -B Studied by Low-Energy Electron Microscopy. <i>Japanese Journal of Applied Physics</i> , 2005 , 44, 358-364	1.4	7
64	Thermal decay of superheated $\sqrt{3}\times\sqrt{3}$ islands and supercooled 1×1 vacancy islands on Si(111). <i>Physical Review B</i> , 2005 , 72,	3.3	6
63	Site-controlled InP nanowires grown on patterned Si substrates. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , 2004 , 24, 133-137	3	28

62	Structural and morphological changes on surfaces with multiple phases studied by low-energy electron microscopy. <i>Applied Surface Science</i> , 2004 , 237, 51-57	6.7	5
61	Step wandering due to the gap in diffusion coefficient on the upper and the lower terraces. <i>Surface Science</i> , 2003 , 522, 64-74	1.8	16
60	Step wandering induced by homoepitaxy on Si(111) during $\sqrt{3}\times\sqrt{3}$ phase transition. <i>Surface Science</i> , 2003 , 527, L222-L228	1.8	20
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53	Enhanced terrace stability for preparation of step-free Si(001)-(2 x 1) surfaces. <i>Physical Review Letters</i> , 2001 , 87, 136103	7.4	12
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49	Observation of Incomplete Surface Melting of Si Using Medium-Energy Ion Scattering Spectroscopy. <i>Japanese Journal of Applied Physics</i> , 2000 , 39, 4421-4424	1.4	6
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38	Sublimation of a heavily boron-doped Si(111) surface. <i>Physical Review B</i> , 1998 , 58, 13146-13150	3.3	32
37	Disordering of Si(111) at high temperatures. <i>Physical Review B</i> , 1998 , 58, 12587-12589	3.3	15
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33	Sublimation of the Si(111) surface in ultrahigh vacuum. <i>Physical Review B</i> , 1997 , 55, R10237-R10240	3.3	64
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23	Patterning-Assisted Control for Ordered Arrangement of Atomic Steps on Si(111) Surfaces. <i>Japanese Journal of Applied Physics</i> , 1995 , 34, L668-L670	1.4	29
22	Real-space observation of (111) facet formation on vicinal Si(111) surfaces. <i>Physical Review B</i> , 1995 , 51, 7753-7761	3.3	17
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20	Exchanges between Si and Pb adatoms on Si(111). <i>Surface Science</i> , 1995 , 328, L547-L552	1.8	10
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16	Trace of interface reconstruction in Ge solid-phase epitaxy on Si(111). <i>Physical Review B</i> , 1994 , 49, 5765-5768	3.5	10
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